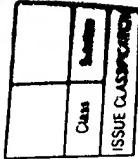


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**U.S. UTILITY** Patent Application

	O.I.P.E.	PATENT DATE
SCANNED <u>M1</u>	O.A. <u>1/1/14</u>	

APPLICATION NO.	CONT/PRIOR	CLASS	SUBCLASS	ART UNIT	EXAMINER
09/981848	F	117		1765	AJ250N

## APPlicants

Seiji Sarayama  
Masahiko Shimada  
Hisanori Yamane  
Masato Aoki

TITLE

Crystal growth method, crystal growth apparatus, group-III nitride crystal and group-III nitride semiconductor device

PTO-2040  
12/99

## **ISSUING CLASSIFICATION**

TERMINAL DISCLAIMER	DRAWINGS			CLAIMS ALLOWED	
	Sheets Drwg.	Figs. Drwg.	Print Fig.	Total Claims	Print Claim for O.G.
<input type="checkbox"/> The term of this patent subsequent to _____ (date) has been disclaimed.  _____  _____				<b>NOTICE OF ALLOWANCE MAILED</b>	
<input type="checkbox"/> The term of this patent shall not extend beyond the expiration date of U.S Patent. No. _____  _____  _____				<b>ISSUE FEE</b>	
<input type="checkbox"/> The terminal ____ months of this patent have been disclaimed.				Amount Due	Date Paid
				<b>ISSUE BATCH NUMBER</b>	
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